

Improved Bipolar Junction Transistor

ABSTRACT OF THE INVENTION

An improved BJT is described that maximizes both B_{VCEO} and F_t/F_{max} for optimum performance. Scattering centers are introduced in the collector region (80) of the BJT to improve B_{VCEO} . The inclusion of the scattering centers allows the width of the collector region W_{CD} (90) to be reduced leading to an improvement in F_t/F_{max} .

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